

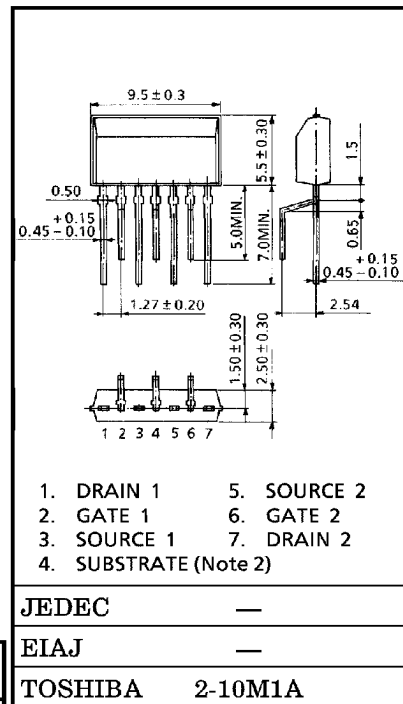
TOSHIBA DUAL FIELD EFFECT TRANSISTOR SILICON MONOLITHIC N CHANNEL JUNCTION TYPE

2SK389

LOW NOISE AUDIO AND DIFFERENTIAL AMPLIFIER APPLICATIONS.

Unit in mm

- 1 Chip Dual Type.
- Recommended for First Differential Stages of DC Amplifiers.
- Very High $|Y_{fs}|$: $|Y_{fs}|=20\text{mS}$ (Typ.)
($V_{DS}=10\text{V}$, $V_{GS}=0$, $f=1\text{kHz}$, $I_{DSS}=3\text{mA}$)
- Good Pair Characteristics
- High Breakdown Voltage : $V_{GDS}=-50\text{V}$ (Min.)
- Very Low Noise : $NF=0.5\text{dB}$ (Typ.)
($V_{DS}=10\text{V}$, $I_D=1\text{mA}$, $R_G=1\text{k}\Omega$, $f=1\text{kHz}$)
- High Input Impedance : $I_{GSS}=-1.0\text{nA}$ (Max.) ($V_{GS}=-30\text{V}$)
- Complementary to 2SJ109



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDS}	-50	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C

Weight : 0.37g (Typ.)

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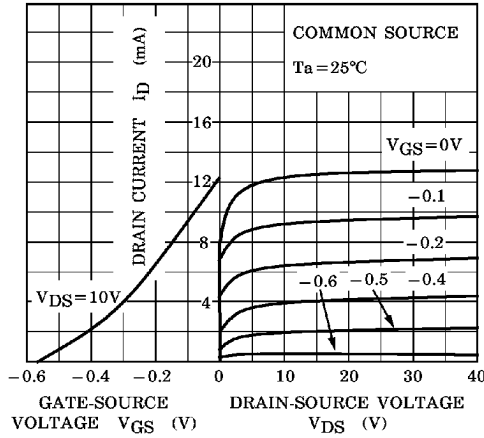
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	I_{GSS}	$V_{GS} = -30V, V_{DS} = 0$	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$V_{DS} = 0, I_G = -100\mu A$	-50	—	—	V
Drain Current	I_{DSS} (Note 1)	$V_{DS} = 10V, V_{GS} = 0$	2.6	—	20	mA
Drain Current Ratio	$I_{DSS}^{(small)} / I_{DSS}^{(large)}$	$V_{DS} = 10V, V_{GS} = 0$	0.9	—	—	—
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS} = 10V, I_D = 0.1\mu A$	-0.15	—	-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, V_{GS} = 0$ $f = 1kHz, I_{DSS} = 3mA$	8	20	—	mS
Forward Transfer Admittance Ratio	$ Y_{fs}^{(small)} / Y_{fs}^{(large)} $	$V_{DS} = 10V, V_{GS} = 0,$ $f = 1kHz$	0.9	—	—	—
Differential Gate-Source Voltage	$ V_{GS1} - V_{GS2} $	$V_{DS} = 10V, I_D = 1mA$	—	—	20	mV
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0,$ $f = 1MHz$	—	25	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{GD} = -10V, I_D = 0,$ $f = 1MHz$	—	5.5	—	pF
Noise Figure	NF (1)	$V_{DS} = 10V, R_G = 1k\Omega$ $I_D = 1mA, f = 10Hz$	—	1.5	10	dB
	NF (2)	$V_{DS} = 10V, R_G = 1k\Omega$ $I_D = 1mA, f = 1kHz$	—	0.5	2	dB

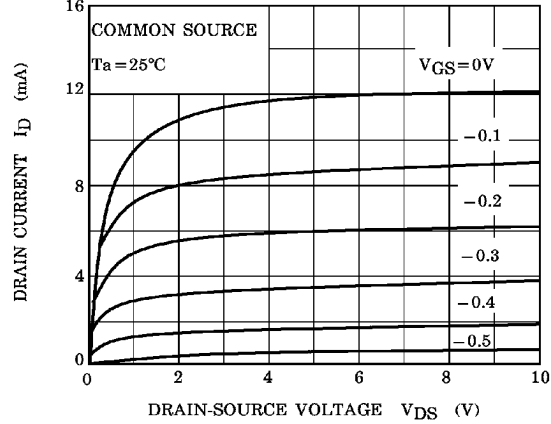
Note 1 : I_{DSS} Classification GR: 2.6~6.5mA, BL: 6~12mA, V: 10~20mA

Note 2 : Use the substrate lead with open.

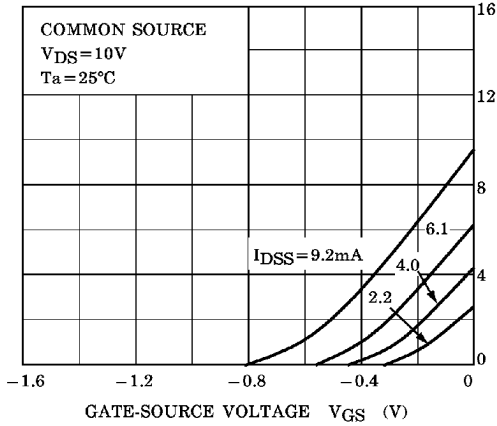
STATIC CHARACTERISTICS



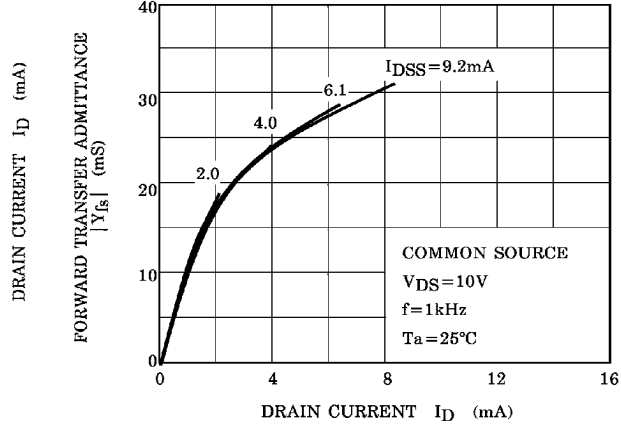
ID - VDS (LOW VOLTAGE REGION)



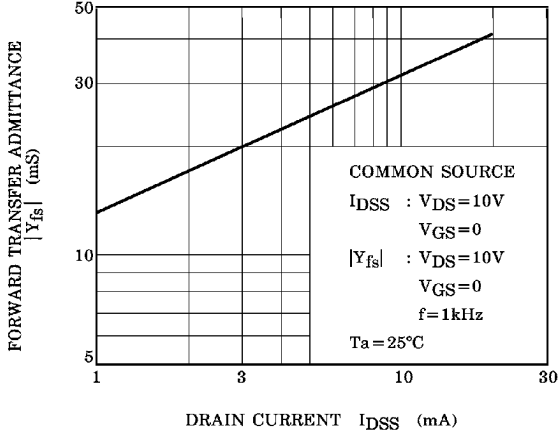
ID - VGS



|Yfs| - ID



|Yfs| - IDSS



VGS(OFF) - IDSS

